Schottky Barrier Diode

RB500V-40

●Applications

Low current rectification

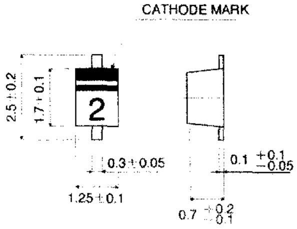
●Features

1)Designed for mounting on small surface areas (UMD2)
2)High reliability

●Construction

Silicon epitaxial

●External dimensions (Units: mm)



UMD2

●Absolute maximum ratings (Ta=25℃)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	45	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−40~125	℃

* 60 Hz for 1 ∿

●Electrical characteristics (Ta=25℃)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	−	0.37	0.45	V	I_F=10mA
Reverse current	I_R	−	0.07	1	μA	V_R=10V
Capacitance between terminals	C_T	−	6.0	−	pF	V_R=10V, f=1MHz

* Special precautions required concerning static electricity when being handled.

●Electrical characteristic curves (Ta=25°C)

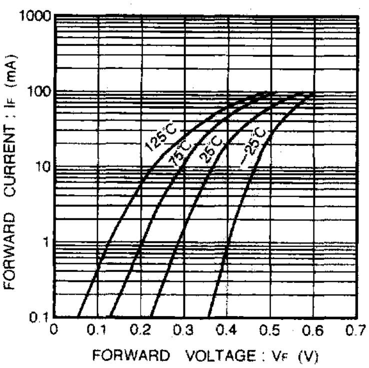


Fig. 1 Forward temperature characteristic

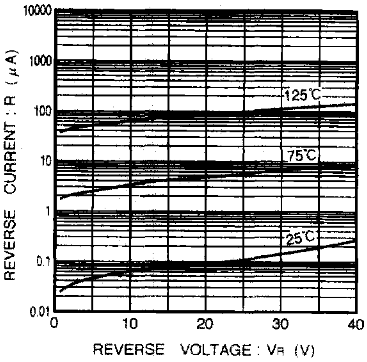


Fig. 2 Reverse temperature characteristic

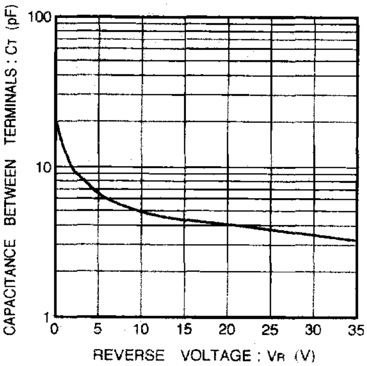


Fig. 3 Capacitance between terminals characteristic